

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (currently amended) An integrated circuit for a data carrier, comprising:
  - a first terminal and a second terminal, wherein the two terminals are provided for connection with transmission means of the data carrier,
  - an ESD protection circuit, which is connected between the two terminals and which comprises a series connection consisting of a first protection diode and a protection stage, which protection stage may be brought from a blocking state into a conductive state by exceeding a voltage threshold, and which comprises a second protection diode connected in parallel with the series connection and in opposition to the first protection diode of the series connection, and
  - a rectifier circuit, which is connected to the ESD protection circuit and comprises a rectifier diode connected in parallel with the ESD protection circuit,

wherein the rectifier diode of the rectifier circuit takes the form of a pure Schottky diode with a parasitic p/n junction and wherein the pure Schottky diode with the parasitic p/n junction simultaneously forms the second protection diode of the ESD protection circuit.
2. (previously presented) An integrated circuit as claimed in claim 1, wherein the rectifier circuit takes the form of a voltage doubler circuit.
3. (currently amended) A data carrier for contactless communication with a communications station, which data carrier comprises:
  - transmission means and
  - an integrated circuit connected with the transmission means, which integrated circuit comprises:

a first terminal and a second terminal, wherein the two terminals are connected with the transmission means,

an ESD protection circuit, which is connected between the two terminals and which comprises a series connection consisting of a first protection diode and a protection stage, which protection stage may be brought from a blocking state into a conductive state by exceeding a voltage threshold, and which comprises a second protection diode connected in parallel with the series connection and in opposition to the first protection diode of the series connection, and

a rectifier circuit, which is connected to the ESD protection circuit and comprises a rectifier diode connected in parallel with the ESD protection circuit,

wherein the rectifier diode of the rectifier circuit takes the form of a pure Schottky diode with a parasitic p/n junction and wherein the pure Schottky diode with the parasitic p/n junction simultaneously forms the second protection diode of the ESD protection circuit.

4. (previously presented) A data carrier as claimed in claim 3, wherein the rectifier circuit takes the form of a voltage doubler circuit.

5. (canceled)

6. (canceled)

7. (previously presented) An integrated circuit as claimed in claim 1, wherein the rectifier circuit further comprises a second rectifier diode that takes the form of a Schottky diode.

8. (previously presented) An integrated circuit as claimed in claim 7, wherein the rectifier circuit further comprises a third rectifier diode and a fourth rectifier diode, wherein the third and fourth rectifier diodes each take the form of a Schottky diode.

9. (previously presented) A data carrier as claimed in claim 3, wherein the rectifier circuit further comprises a second rectifier diode that takes the form of a Schottky diode.

10. (previously presented) A data carrier as claimed in claim 9, wherein the rectifier circuit further comprises a third rectifier diode and a fourth rectifier diode, wherein the third and fourth rectifier diodes each take the form of a Schottky diode.